

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A method for manufacturing a contact plug of a semiconductor device, the method comprising:
 - forming a wordline pattern ~~having with~~ a sequentially stacked structure of a wordline conductive material and a hard mask nitride film on a semiconductor substrate;
 - forming a ~~nitride film~~ spacer on a side of the wordline pattern;
 - forming a planarized interlayer insulating film covering the resultant structure on the wordline pattern;
 - selectively etching the interlayer insulating film to form a contact hole;
 - forming a polysilicon layer on the entire surface of the resultant structure ~~surface of the interlayer insulating film where the contact hole is formed;~~ and
 - performing a chemical mechanical polishing (CMP) process on the ~~polysilicon layer and the interlayer insulating film~~ resultant structure until the word line pattern hard mask nitride film is exposed using an acidic oxide film CMP slurry ~~on the polysilicon layer and interlayer insulating film, the acidic oxide film CMP slurry, wherein the slurry having has a~~ pH ranging from 2 to 7 and containing contains an oxidizer selected from the group consisting of hydrogen peroxide (H_2O_2), periodic acid (H_2IO_6), ferric nitrate [$Fe(N_3O_9)$] and combination combinations thereof until the ~~hard mask nitride film is exposed,~~ making the etching ratio between polysilicon and interlayer insulating film substantially same.
2. (Canceled)
3. (Original) The method according to claim 1, wherein the oxidizer is present in an amount ranging from 1 to 40 vol% based on the CMP slurry.

4. (Original) The method according to claim 1, wherein the oxidizer is present in an amount ranging from 20 to 30 vol% based on the CMP slurry.

5. (Original) The method according to claim 1, wherein the acidic slurry has pH ranging from 2 to 5.

6. (Currently Amended) The method according to claim 1, wherein the acidic slurry comprises an abrasive selected from the group consisting of silica (SiO_2), ceria (CeO_2), zirconia (ZrO_2), alumina (Al_2O_3), and ~~combination~~ combinations thereof.

7. (Original) The method according to claim 6, wherein the abrasive is present in an amount ranging from 10 to 50 wt% based on the CMP slurry.

8. (Original) The method according to claim 7, wherein the abrasive is present in an amount ranging from 25 to 35 wt% based on the CMP slurry.

9. (Original) The method according to claim 1, wherein the polysilicon layer is formed using one selected from the group consisting of P-doped amorphous silicon film, P-doped polysilicon film, P-doped epitaxial silicon film, and combinations thereof.

10. (Canceled)

11. (Original) The method according to claim 1, wherein the interlayer insulating film is formed of a BPSG (borophosphosilicate glass) or HDP (high density plasma) oxide film.

12. (Currently Amended) A method for manufacturing a contact plug of a semiconductor device, the method comprising:

forming a wordline pattern having with a sequentially stacked of a wordline conductive material and a hard mask nitride film on a semiconductor substrate;

forming a ~~nitride film~~ spacer on a side of the wordline pattern;

forming a planarized interlayer insulating film covering the resultant structure on the wordline pattern;

selectively etching the interlayer insulating film on a partial region until the substrate is exposed to form a contact hole;

forming a polysilicon layer on the entire surface of the resultant structure surface of the interlayer insulating film where the contact hole is formed; and

performing a chemical mechanical polishing CMP process on the resultant structure until the wordline pattern is exposed ~~the polysilicon layer and the interlayer insulating film~~ using an acidic oxide film CMP slurry ~~on the polysilicon layer and the interlayer insulating film, wherein the acidic oxide film CMP slurry having~~ has [a] pH ranging 2 to 7 containing and contains H_2O_2 in an amount ranging from 1 to 40 vol%, making the etching ratio between polysilicon and interlayer insulating film substantially same.

13. (Previously Presented) The method according to claim 12, wherein the H_2O_2 is present in an amount ranging from 20 to 30 vol% based on the CMP slurry.

14. (Original) The method according to claim 12, wherein the acidic slurry has a pH ranging from 2 to 5.

15. (Original) The method according to claim 12, wherein the acidic slurry comprises an abrasive selected from the group consisting of silica (SiO_2), ceria (CeO_2), zirconia (ZrO_2), alumina (Al_2O_3), and combinations thereof.
16. (Original) The method according to claim 15, wherein the abrasive is present in an amount ranging from 10 to 50 wt% based on the CMP slurry.
17. (Original) The method according to claim 15, wherein the abrasive is present in an amount ranging from 25 to 35 wt% based on the CMP slurry.
18. (Original) The method according to claim 12, wherein the polysilicon layer is formed using one selected from the group consisting of P-doped amorphous silicon film, P-doped polysilicon film, P-doped epitaxial silicon film, and combinations thereof.
19. (Original) The method according to claim 12, wherein the wordline conductive material is formed of a SiON or organic bottom ARC layer.
20. (Original) The method according to claim 12, wherein the interlayer insulating film is formed of a BPSG (borophosphosilicate glass) or HDP (high density plasma) oxide film.

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